

L Number	Hits	Search Text	DB	Time stamp
1	2937	257/664 or 257/700 or 257/728	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 15:50
2	33	(257/664 or 257/700 or 257/728) and impedance near12 (tailor or tailored or adjust or adjustment)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 15:52
3	8	(257/664 or 257/700 or 257/728) and impedance near12 (tailor or tailored or adjust or adjustment) and (length or number) near12 wire	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 16:16
4	325	impedance near12 (tailor or tailored or adjust or adjustment) and (length or number) near12 wire	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 16:17
5	227	impedance near6 (tailor or tailored or adjust or adjustment) and (length or number) near6 wire	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 16:18
6	11	impedance near4 (tailor or tailored or adjust or adjustment) and (length or number) near4 wire and (variance or rms or root-mean-square or root adj mean adj square)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 16:19
-	1630	power adj transistor.ti,ab. and amplifier.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/11 07:55
-	222	power adj transistor.ti. and amplifier.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 08:48
-	23	power adj transistor.ti. and amplifier.ti. and (rf or radio adj frequency).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 10:05
-	126	power adj transistor.ti. and (rf or radio adj frequency).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 10:07
-	87	power adj transistor.ti. and (rf or radio adj frequency).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 10:30
-	220	internal adj matching	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 10:31
-	48	internal adj matching with transistor.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 10:34
-	0	(internal adj matching with transistor.ti,ab.) and ldmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 10:35

updated.

-	0	(internal adj matching with transistor.ti,ab.) and ldmosfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 10:35
-	0	(internal adj matching with transistor.ti,ab.) and mosfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 10:35
-	12	(internal adj matching with transistor.ti,ab.) and field adj effect adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 10:35
-	0	JP-2001024148 JP-05218102 JP-04321308 JP-01283951 JP-02005459 JP-01199436 JP-63086904 JP-55091148	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 12:12
-	14	JP-05218102\$-\$.did. JP-04321308\$-\$.did. JP-01283951\$-\$.did. JP-02005459\$-\$.did. JP-01199436\$-\$.did. JP-63086904\$-\$.did. JP-55091148\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 12:13
-	10	((("5371405") or ("6281756") or ("5576661") or ("5206608") or ("5206608"))).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 12:14
-	4	EP-680141\$-\$.did. JP-01050602\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 12:15
-	0	((JP-05218102\$-\$.did. JP-04321308\$-\$.did. JP-01283951\$-\$.did. JP-02005459\$-\$.did. JP-01199436\$-\$.did. JP-63086904\$-\$.did. JP-55091148\$-\$.did.) or (((("5371405") or ("6281756") or ("5576661") or ("5206608") or ("5206608"))).PN.) or (EP-680141\$-\$.did. JP-01050602\$-\$.did.)) and substrate and transistor and input adj matching and lead and wir\$3 and impedance and (die or dice or chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 12:17
-	0	((JP-05218102\$-\$.did. JP-04321308\$-\$.did. JP-01283951\$-\$.did. JP-02005459\$-\$.did. JP-01199436\$-\$.did. JP-63086904\$-\$.did. JP-55091148\$-\$.did.) or (((("5371405") or ("6281756") or ("5576661") or ("5206608") or ("5206608"))).PN.) or (EP-680141\$-\$.did. JP-01050602\$-\$.did.)) and substrate and transistor and input adj matching and lead and wir\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 12:17

-	8	((JP-05218102\$-\$\$.did. JP-04321308\$-\$\$.did. JP-01283951\$-\$\$.did. JP-02005459\$-\$\$.did. JP-01199436\$-\$\$.did. JP-63086904\$-\$\$.did. JP-55091148\$-\$\$.did.) or (((("5371405") or ("6281756") or ("5576661") or ("5206608") or ("5206608")).PN.) or (EP-680141\$-\$\$.did. JP-01050602\$-\$\$.did.)) and substrate and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 12:17
-	8	((JP-05218102\$-\$\$.did. JP-04321308\$-\$\$.did. JP-01283951\$-\$\$.did. JP-02005459\$-\$\$.did. JP-01199436\$-\$\$.did. JP-63086904\$-\$\$.did. JP-55091148\$-\$\$.did.) or (((("5371405") or ("6281756") or ("5576661") or ("5206608") or ("5206608")).PN.) or (EP-680141\$-\$\$.did. JP-01050602\$-\$\$.did.)) and substrate and transistor and match\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 12:17
-	2	((JP-05218102\$-\$\$.did. JP-04321308\$-\$\$.did. JP-01283951\$-\$\$.did. JP-02005459\$-\$\$.did. JP-01199436\$-\$\$.did. JP-63086904\$-\$\$.did. JP-55091148\$-\$\$.did.) or (((("5371405") or ("6281756") or ("5576661") or ("5206608") or ("5206608")).PN.) or (EP-680141\$-\$\$.did. JP-01050602\$-\$\$.did.)) and substrate and transistor and match\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 12:18
-	2	((JP-05218102\$-\$\$.did. JP-04321308\$-\$\$.did. JP-01283951\$-\$\$.did. JP-02005459\$-\$\$.did. JP-01199436\$-\$\$.did. JP-63086904\$-\$\$.did. JP-55091148\$-\$\$.did.) or (((("5371405") or ("6281756") or ("5576661") or ("5206608") or ("5206608")).PN.) or (EP-680141\$-\$\$.did. JP-01050602\$-\$\$.did.)) and substrate and transistor and match\$3 and lead\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 12:18
-	2	((JP-05218102\$-\$\$.did. JP-04321308\$-\$\$.did. JP-01283951\$-\$\$.did. JP-02005459\$-\$\$.did. JP-01199436\$-\$\$.did. JP-63086904\$-\$\$.did. JP-55091148\$-\$\$.did.) or (((("5371405") or ("6281756") or ("5576661") or ("5206608") or ("5206608")).PN.) or (EP-680141\$-\$\$.did. JP-01050602\$-\$\$.did.)) and substrate and transistor and match\$3 and lead\$1 and wir\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 13:41
-	1	((JP-05218102\$-\$\$.did. JP-04321308\$-\$\$.did. JP-01283951\$-\$\$.did. JP-02005459\$-\$\$.did. JP-01199436\$-\$\$.did. JP-63086904\$-\$\$.did. JP-55091148\$-\$\$.did.) or (((("5371405") or ("6281756") or ("5576661") or ("5206608") or ("5206608")).PN.) or (EP-680141\$-\$\$.did. JP-01050602\$-\$\$.did.)) and (wir\$3 with impedance)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 13:43

-	4393	(wir\$3 with impedance).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 13:43
-	207	(wir\$3 with impedance).ti,ab. and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 13:44
-	13	(bonding adj2 wir\$3 near5 impedance).ti,ab. and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 16:39
-	3	5371405.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 16:40
-	2	6281756.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 16:42
-	545	257/664	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 16:43
-	27	(JP-05218102\$-\$\$.did. JP-04321308\$-\$\$.did. JP-01283951\$-\$\$.did. JP-02005459\$-\$\$.did. JP-01199436\$-\$\$.did. JP-63086904\$-\$\$.did. JP-55091148\$-\$\$.did.) or (((("5371405") or ("6281756") or ("5576661") or ("5206608") or ("5206608"))).PN.) or (EP-680141\$-\$\$.did. JP-01050602\$-\$\$.did.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 16:44
-	0	jp-404048756\$-\$\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 16:45
-	2	jp-04048756\$-\$\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 16:48
-	1768	257/700	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 16:48
-	742	257/728	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 16:48
-	16	(257/664 or 257/700 or 257/728) and wir\$3 and substrate and power adj transistor and matching and impedance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/10 16:50
-	212	trench same gate same high adj voltage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/11 07:57

-	46	trench same gate same high adj voltage and field adj effect adj transistor and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/11 07:58
-	6	(trench.ti,ab. same gate same high adj voltage) and field adj effect adj transistor and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/11 07:59